

REMARKS/ARGUMENTS

The above-identified patent application has been reviewed in light of the Examiner's Action dated August 18, 2004. Claims 1-6 have been previously withdrawn and Claims 13-17 have been previously cancelled, without intending to abandon or to dedicate to the public any patentable subject matter. Accordingly, Claims 7-12 are pending in the application, which have been rejected under 35 USC §103(a) as being unpatentable over U.S. Patent No. 5,548,132 to Batra et al. ("Batra") in view of US Patent No. 4,975,760 to Dohjo et al. ("Dohjo"). Applicants respectfully traverse these rejections in light of the amendments and arguments presented herein and thus request reconsideration and withdrawal of the rejections of the claims.

Applicants assert that Batra does not disclose grain sizes of the drain and the source that are set greater than a grain size of the channel based on energy of laser light irradiated on a surface of an amorphous silicon film to form a polycrystalline silicon film as recited in independent Claims 7 and 8. Rather, Batra discloses a grain size of the drain offset region 66 that is set greater than a grain size of the remaining region of the thin film transistor layer 60 other than the drain offset region 66 based on a p-level doping and annealing (see Column 6, Lines 11-20). To establish prima facie obviousness of a claimed invention, all the claim limitations must be taught or suggested by the prior art. *MPEP §2143.03*. Since Batra does not teach the requisite grain size difference, Applicants respectfully request withdrawal of the rejection of independent Claims 7 and 8. If an independent claim is nonobvious under 35 U.S.C. §103, then any claim depending therefrom is nonobvious. *Id.* Thus, Applicants respectfully request the withdrawal of the rejections of Claims 9-12.


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Dohjo discloses forming a gate electrode using an Mo-Ta alloy. However, Dohjo does not disclose that grain sizes of the drain and the source are set greater than the grain size of the channel based on energy of laser light irradiated on a surface of an amorphous silicon film to form a polycrystalline silicon film as recited in Claims 7 and 8. Thus, Applicants respectfully request the withdrawal of the rejections based upon Batra in view of Dohjo.

Based upon the foregoing, Applicants believe that all pending claims are in condition for allowance and such disposition is respectfully requested. In the event that a telephone conversation would further prosecution and/or expedite allowance, the Examiner is invited to contact the undersigned.

Respectfully submitted,

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